

#3/Pre-B
A. Paul
11/28/00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

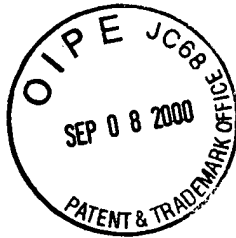
In re Application of:

Yusuke Kohyama et al.

Serial No.: 09/631,830

Filed: August 3, 2000

For: **STACKED CAPACITOR-TYPE SEMICONDUCTOR
STORAGE DEVICE AND MANUFACTURING
METHOD THEREOF**



Atty. Docket: 1701.00021

Art Unit: 2835

Examiner: H. Duong

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SECOND PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to examination on the merits, please amend the above-identified application as follows:

IN THE CLAIMS:

Please add the following new claims 30-39:

~~11-30.~~ A method of manufacturing a semiconductor device comprising the steps of:

- forming a first insulating layer on a semiconductor substrate;
- forming first and second wirings on said first insulating layer at a predetermined interval, said first and second wirings including a conductive film and a first insulating film on said conductive film;
- forming a second insulating film on said first insulating layer;
- forming a line/space pattern on said second insulating film, said line/space pattern being intersected perpendicularly to said first and second wirings; and

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